



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

SCH1335 — General-Purpose Switching Device Applications

Features

- 1.8V drive
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		-12	V
Gate-to-Source Voltage	V_{GS}		±10	V
Drain Current (DC)	I_D		-2.5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	-10	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm ² ×0.8mm)	0.8	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

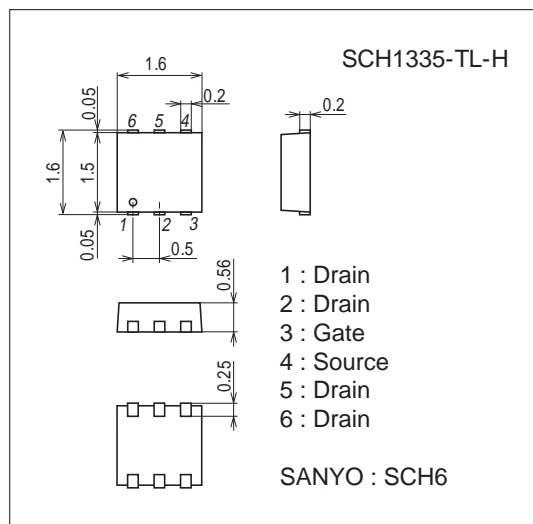
This product is designed to "ESD immunity < 200V**", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

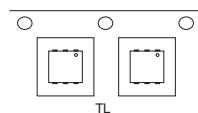
7028-002



Product & Package Information

- Package : SCH6
- JEITA, JEDEC : SOT-563
- Minimum Packing Quantity : 5,000 pcs./reel

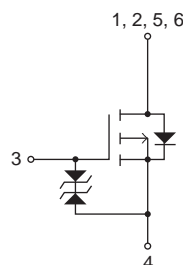
Packing Type : TL



Marking



Electrical Connection

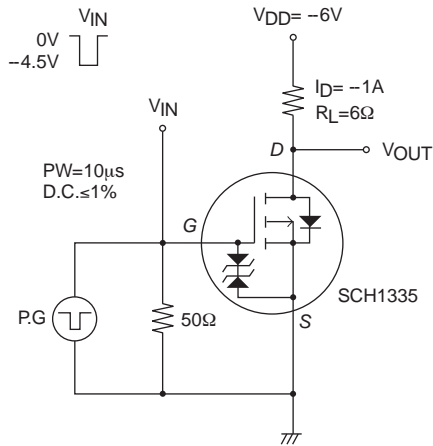


SCH1335

Electrical Characteristics at Ta=25°C

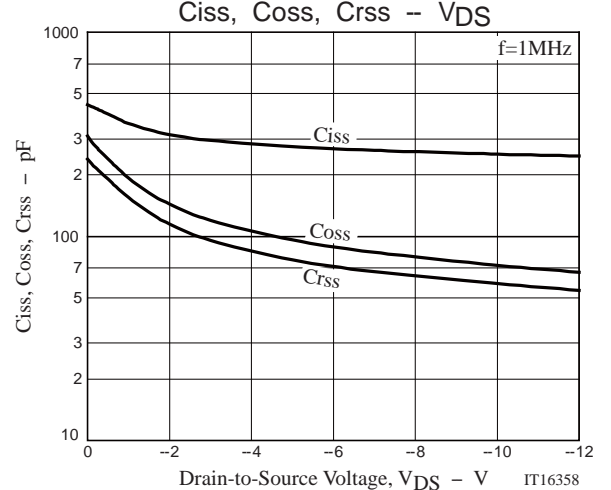
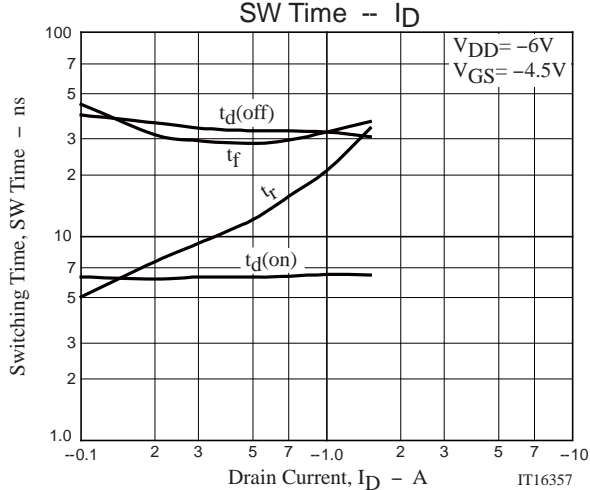
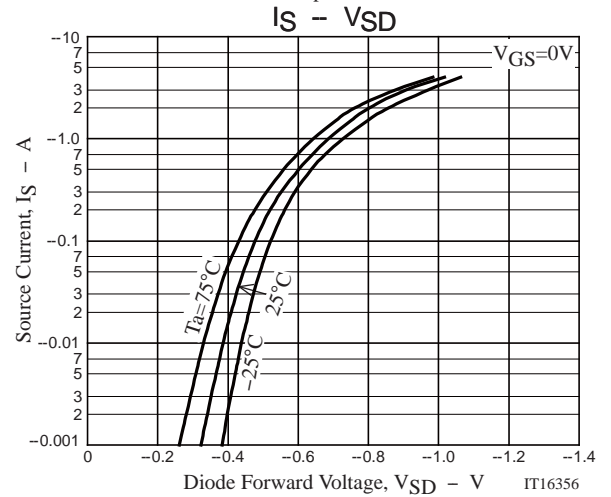
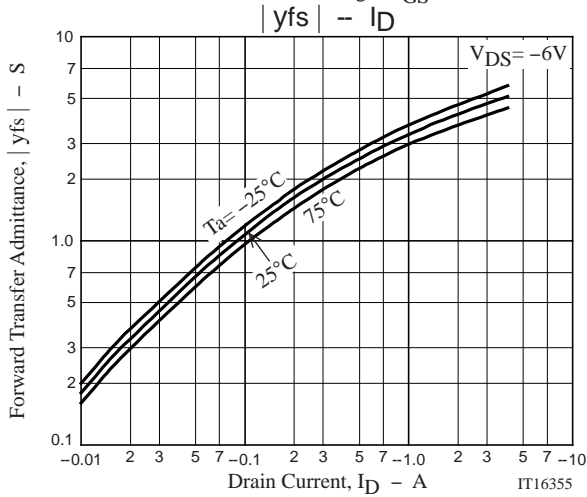
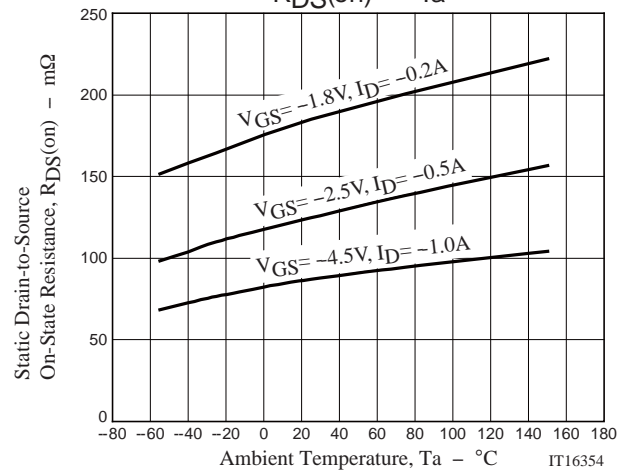
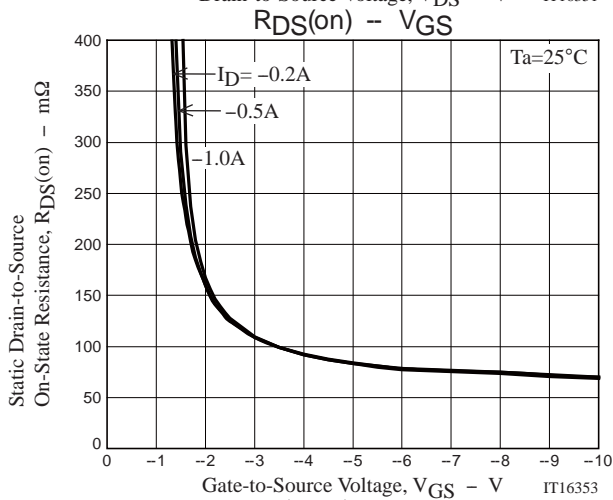
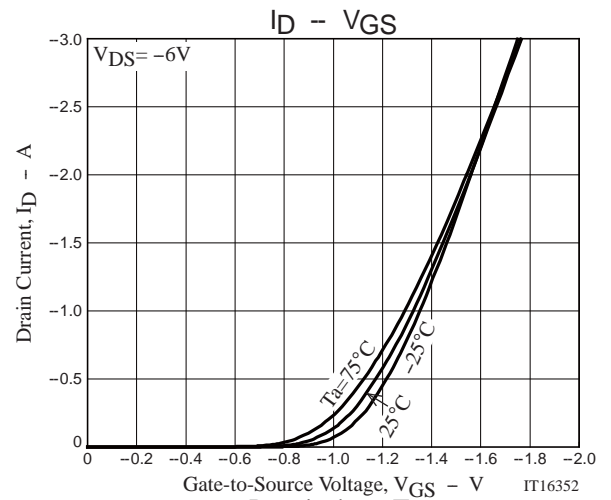
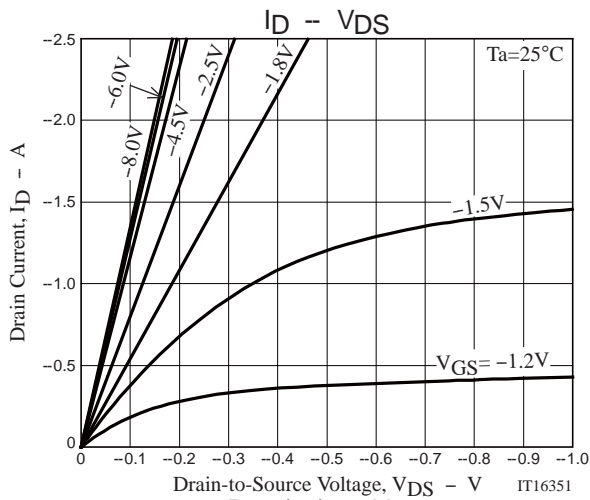
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0V$	-12			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V$			-10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8V, V_{DS} = 0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -6V, I_D = -1mA$	-0.4		-1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -6V, I_D = -1A$		3.3		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -1A, V_{GS} = -4.5V$		86	112	$m\Omega$
	$R_{DS(on)2}$	$I_D = -0.5A, V_{GS} = -2.5V$		125	175	$m\Omega$
	$R_{DS(on)3}$	$I_D = -0.2A, V_{GS} = -1.8V$		185	285	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -6V, f = 1MHz$		270		pF
Output Capacitance	C_{oss}			90		pF
Reverse Transfer Capacitance	C_{rss}			72		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		6.5		ns
Rise Time	t_r			21		ns
Turn-OFF Delay Time	$t_d(off)$			33		ns
Fall Time	t_f			33		ns
Total Gate Charge	Q_g	$V_{DS} = -6V, V_{GS} = -4.5V, I_D = -2.5A$		3.1		nC
Gate-to-Source Charge	Q_{gs}			0.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			0.9		nC
Diode Forward Voltage	V_{SD}	$I_S = -2.5A, V_{GS} = 0V$		-0.84	-1.2	V

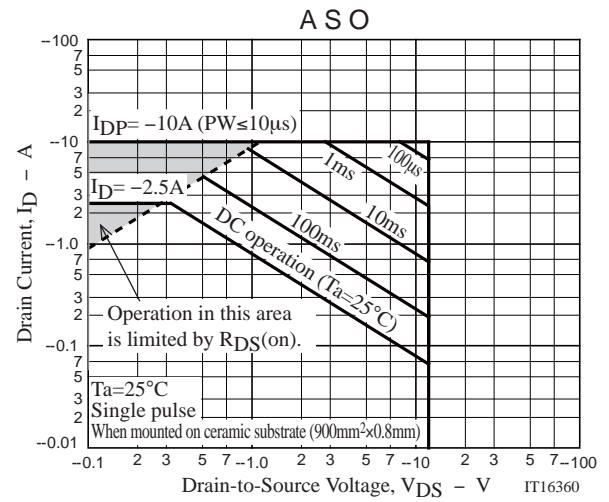
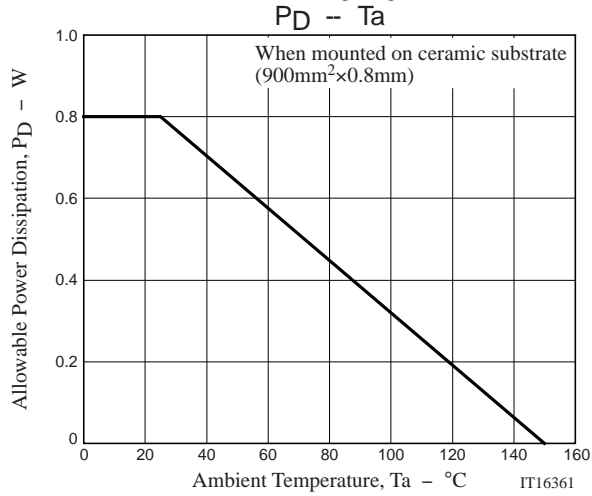
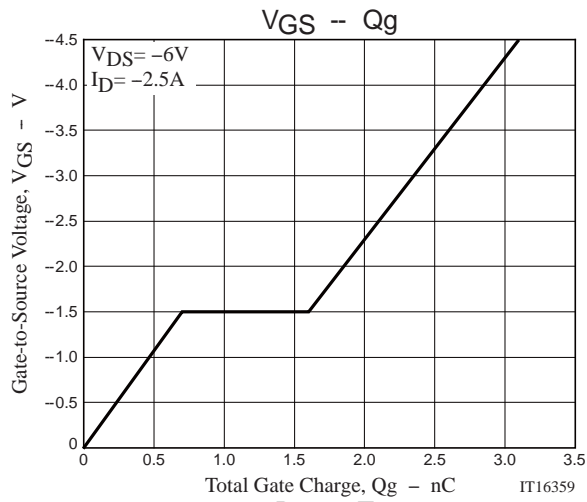
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
SCH1335-TL-H	SCH6	5,000pcs./reel	Pb Free and Halogen Free





Taping Specification

SCH1335-TL-H

1. Packing Format

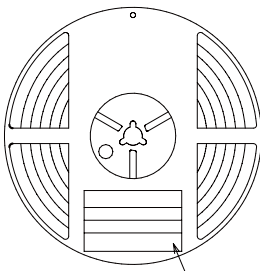
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
SCH6	SCH6	5,000	25,000	150,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit:mm)

Outer box label

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



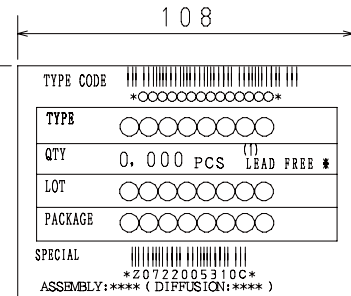
Type No. →

LOT No. →

Quantity →

Origin →

Reel label



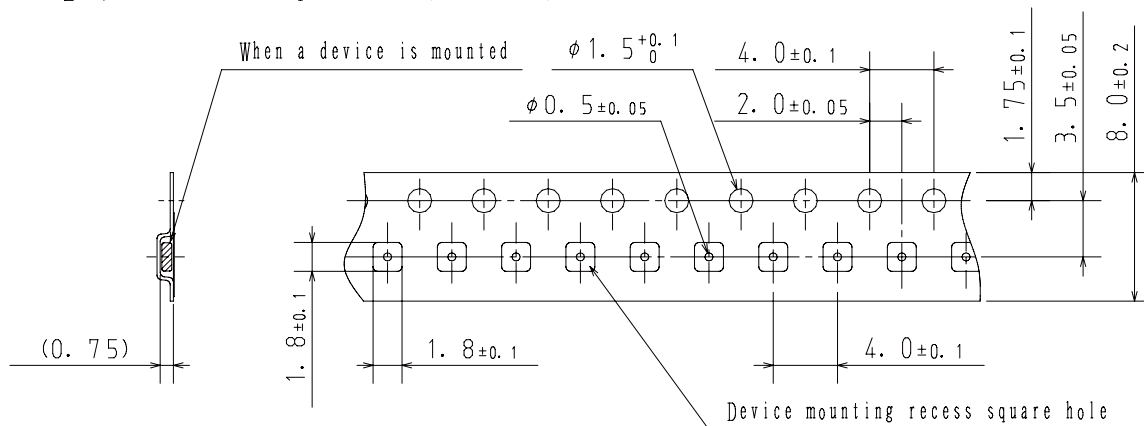
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

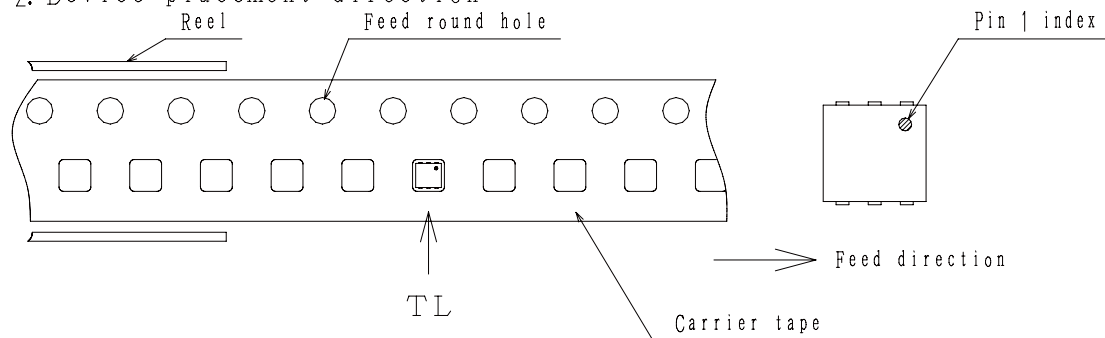
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)

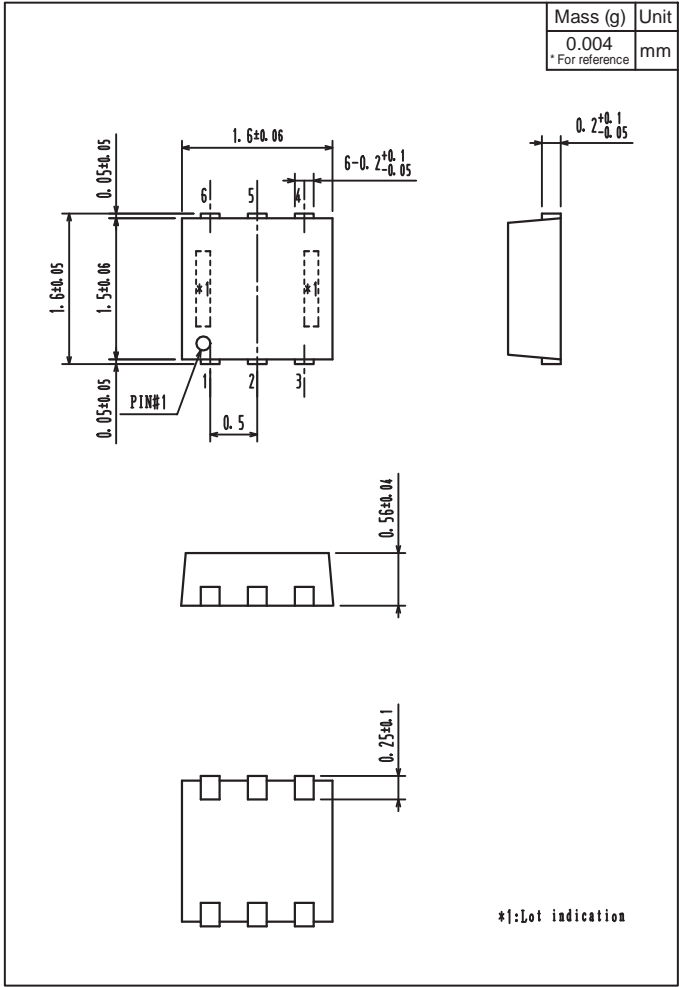


2-2. Device placement direction

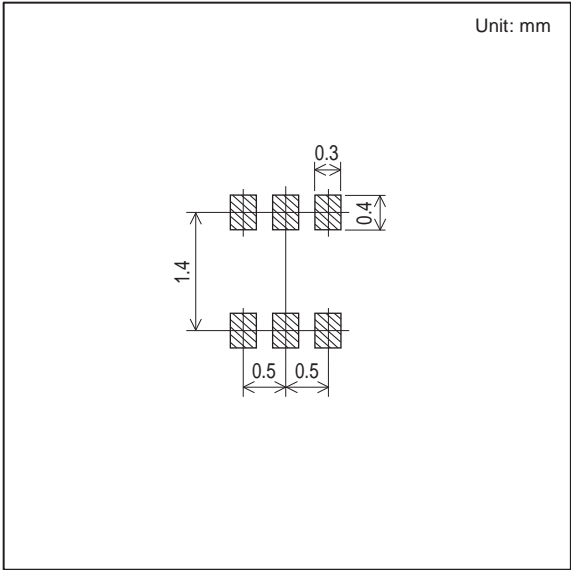


Those with pin 1 index on the feed hole side.....TL

Outline Drawing
SCH1335-TL-H



Land Pattern Example



Note on usage : Since the SCH1335 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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